



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

SURFACE MOUNT
PNP Digital Silicon Transistor

VOLTAGE 50 Volts CURRENT 100 mAmpere

CHDTA144GKPT

APPLICATION

* Switching circuit, Inverter, Interface circuit, Driver circuit.

FEATURE

- * Small surface mounting type. (SC-59/SOT-346)
- * High current gain.
- * Suitable for high packing density.
- * Low collector-emitter saturation.
- * High saturation current capability.
- * Internal isolated PNP transistors in one package.
- * Built in bias resistor(R1=47kΩ, Typ.)

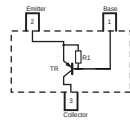
CONSTRUCTION

* One PNP transistors and bias of thin-film resistors in one package.

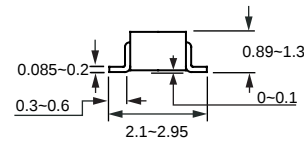
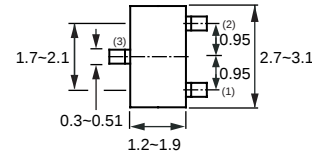
MARKING

GK3

CIRCUIT



SC-59/SOT-346



Dimensions in millimeters

SC-59/SOT-346

LIMITING VALUES

In accordance with the Absolute Maximum Rating System.

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-Base voltage		-50	V
V _{CEO}	Collector-Emitter voltage		-50	V
V _{EB0}	Emitter-Base voltage		-5	V
I _c	Collector current		-100	mA
P _c	Collector Power dissipation	T _{amb} ≤ 25 °C, Note 1	200	mW
T _{STG}	Storage temperature		150	°C
T _j	Junction temperature		-55 ~ +150	°C
R _{θJ-S}	Thermal resistance , Note 1	junction - soldering point	140	°C/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC (CHDTA144GKPT)

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BV _{CBO}	Collector-Base breakdown voltage	I _C = -50uA	-50.0	—	—	V
BV _{CEO}	Collector-Emitter breakdown voltage	I _C = -1mA	-50.0	—	—	V
BV _{EBO}	Emitter-Base breakdown voltage	I _E = -160uA	-5.0	—	—	V
V _{CE(sat)}	Collector-Emitter Saturation voltage	I _C = -10mA; I _B = -0.5mA	—	—	-0.3	V
I _{CBO}	Collector-Base current	V _{CB} = -50V	—	—	-0.5	uA
I _{EBO}	Emitter-Base current	V _{EB} = -4V	—	—	-130	uA
h _{FE}	DC current gain	I _C = -5mA; V _{CE} = -5.0V	68	—	—	
R ₁	Input resistor		32.9	47	61.1	KΩ
f _T	Transition frequency	I _E =5mA, V _{CE} = -10.0V f=100MHz	—	250	—	MHz

Note

1.Pulse test: t_p≤300uS; δ ≤0.02.